



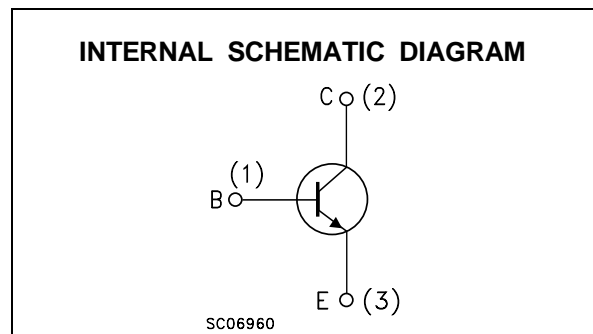
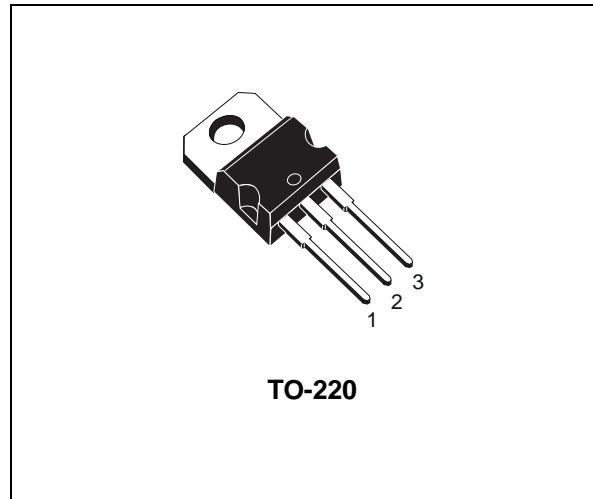
TIP47/TIP48 TIP49/TIP50

SILICON NPN SWITCHING TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- NPN TRANSISTOR

DESCRIPTION

The TIP47, TIP48, TIP49 and TIP50 are silicon Multiepitaxial NPN Planar transistors mounted in Jedec TO-220 plastic package. It is intended for use in linear and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		TIP47	TIP48	TIP49	TIP50	
V_{CB0}	Collector-Base Voltage ($I_E = 0$)	350	400	450	500	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	250	300	350	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5				V
I_C	Collector Current	1				A
I_{CM}	Collector Peak Current	2				A
I_B	Base Current	0.6				A
P_{tot}	Total Dissipation at $T_{case} \leq 25\text{ }^\circ\text{C}$ $T_{amb} \leq 25\text{ }^\circ\text{C}$	40				W
		2				W
T_{stg}	Storage Temperature	-65 to 150				$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150				$^\circ\text{C}$

TIP47 / TIP48 / TIP49 / TIP50

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.125	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP47 V _{CE} = 350 V for TIP48 V _{CE} = 400 V for TIP49 V _{CE} = 450 V for TIP50 V _{CE} = 500 V			1	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP47 V _{CE} = 150 V for TIP48 V _{CE} = 200 V for TIP49 V _{CE} = 250 V for TIP50 V _{CE} = 300 V			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP47 for TIP48 for TIP49 for TIP50	250 300 350 400			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 1 A I _B = 0.2 A			1	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 1 A V _{CE} = 10 V			1.5	V
h _{FE} *	DC Current Gain	I _C = 0.3 A V _{CE} = 10 V I _C = 1 A V _{CE} = 10 V	30 10		150	
f _T	Transition Frequency	V _{CE} = 10 V I _C = 0.2 A f = 2 MHz	10			MHz
h _{fe}	Small Signal Current Gain	V _{CE} = 10 V I _C = 0.2 A f = 1 KHz	25			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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